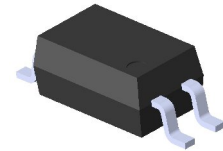
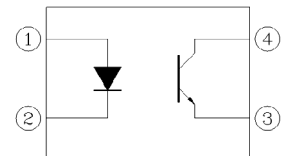


Features:

- Halogens free
- Current transfer ratio
(CTR: 50~600% at $I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$)
(CTR: 40~320% at $I_F = 10\text{mA}$, $V_{CE} = 5\text{V}$)
- High isolation voltage between input and output (Viso=3750 V rms)
- Compact 4 Pin SSOP with a 2.0 mm profile
- Pb free and RoHS compliant.
- UL approved (No. 214129)
- VDE approval (132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved
- CSA approved



Schematic



Description

The EL3H7-G series devices consist of an infrared emitting diode, optically coupled to a phototransistor detector encapsulated with green compound.

They are packaged in a 4-pin small outline SMD package.

Pin Configuration

1. Anode
2. Cathode
3. Emitter
4. Collector

Applications

- DC-DC Converters
- Programmable controllers
- Telecommunication equipments
- Signal transmission between circuits of different potentials and impedances

Absolute Maximum Ratings (T_a=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I _F	50	mA
	Peak forward current (1us, pulse)	I _{FP}	1	A
	Reverse voltage	V _R	6	V
	Power dissipation Derating factor (above T _a = 90°C)	P _D	70	mW
			2.0	mW/°C
Output	Power dissipation Derating factor (above T _a = 70°C)	P _C	150	mW
			3.1	mW/°C
	Collector current	I _C	50	mA
	Collector-Emitter voltage	V _{CEO}	80	V
	Emitter-Collector voltage	V _{ECO}	7	V
Total power dissipation		P _{TOT}	200	mW
Isolation voltage ^{*1}		V _{ISO}	3750	V rms
Operating temperature		T _{OPR}	-55 ~ +110	°C
Storage temperature		T _{STG}	-55 ~ +125	°C
Soldering temperature ^{*2}		T _{SOL}	260	°C

Notes

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1 & 2 are shorted together, and pins 3 & 4 are shorted together.

*2 For 10 seconds.

4 PIN ULTRA SMALL SSOP PHOTOTRANSISTOR PHOTOCOUPLER

EL3H7-G Series

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Forward voltage	V_F	-	1.2	1.4	V	$I_F = 20\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R = 4\text{V}$
Input capacitance	C_{in}	-	30	250	pF	$V = 0, f = 1\text{kHz}$

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Emitter dark current	I_{CEO}	-	-	100	nA	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$
Collector-Emitter breakdown voltage	BV_{CEO}	80	-	-	V	$I_C = 0.1\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	$I_E = 0.1\text{mA}$

Transfer Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Current Transfer ratio	EL3H7	50	-	600	%	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$
	EL3H7A	80	-	160		
	EL3H7B	130	-	260		
	EL3H7C	200	-	400		
	EL3H7D	300	-	600		
	EL3H7E	100	-	200		
	EL3H7F	150	-	300		$I_F = 10\text{mA}, V_{CE} = 5\text{V}$
	EL3H7H	40	-	80		
	EL3H7I	63	-	125		
	EL3H7J	100	-	200		
	EL3H7K	160	-	320		

Transfer Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Emitter saturation voltage	$V_{CE(sat)}$	-	0.1	0.2	V	$I_F = 10\text{mA}$, $I_C = 1\text{mA}$
Isolation resistance	R_{IO}	5×10^{10}	-	-	Ω	$V_{IO} = 500\text{Vdc}$, 40~60% R.H.
Floating capacitance	C_{IO}	-	0.3	1.0	pF	$V_{IO} = 0$, $f = 1\text{MHz}$
Rise time	t_r	-	5	18	μs	$V_{CE} = 2\text{V}$, $I_C = 2\text{mA}$, $R_L = 100\Omega$
Fall time	t_f	-	3	18	μs	

* Typical values at $T_a = 25^{\circ}\text{C}$

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Typical Performance Curves

Figure 1. Forward Current vs Forward Voltage

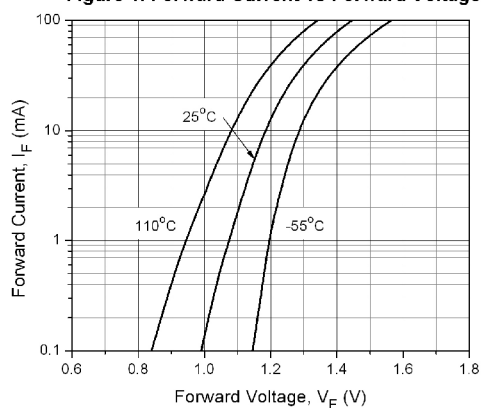


Figure 2. Normalized Collector Current vs Forward Current

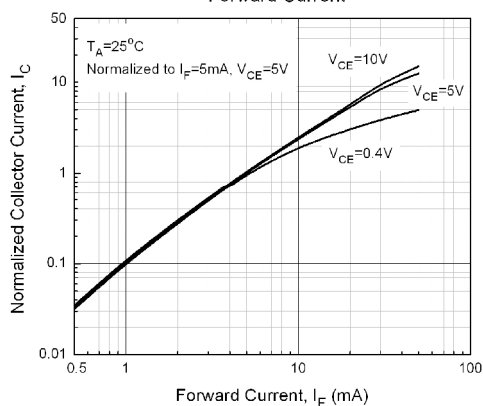


Figure 3. Normalized Current Transfer Ratio vs Forward Current

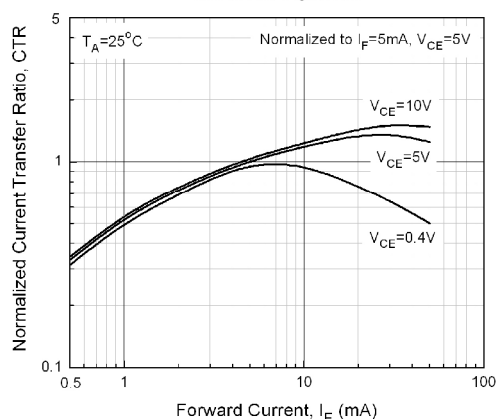


Figure 4. Normalized Collector Current vs Ambient Temperature

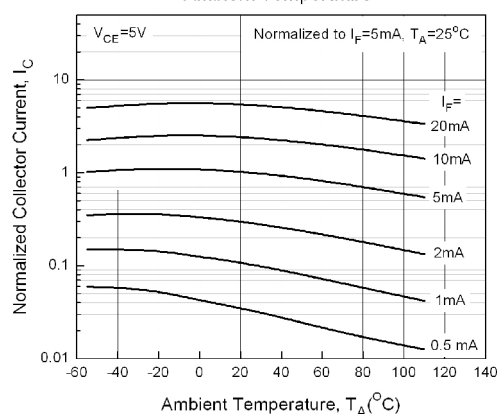


Figure 5. Normalized Current Transfer Ratio vs Ambient Temperature

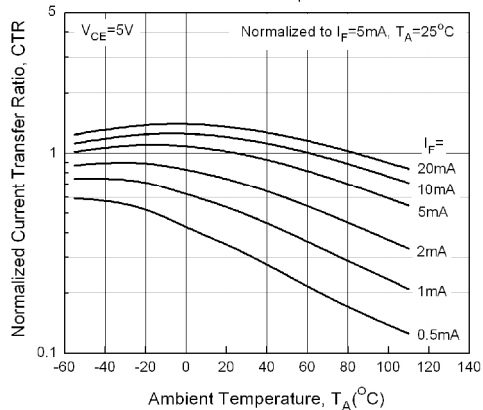


Figure 6. Collector Current vs Collector-Emitter Voltage

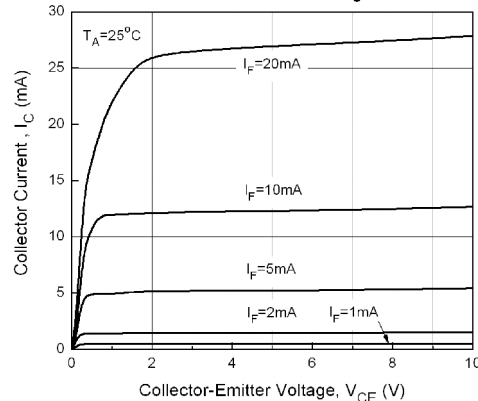


Figure 7. Collector Current vs Collector-Emitter Voltage

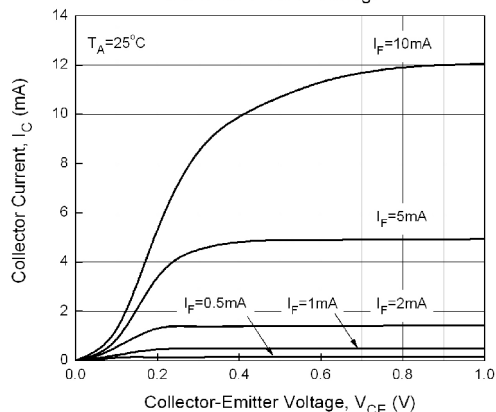


Figure 8. Collector Dark Current vs Ambient Temperature

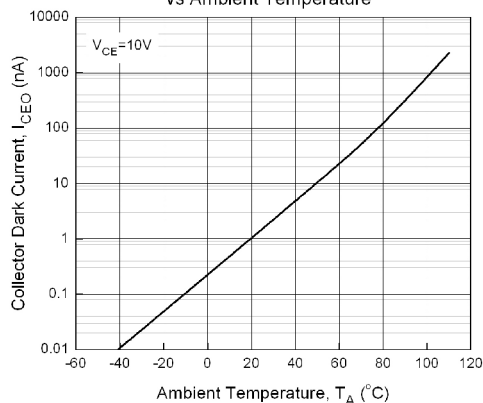


Figure 9. Collector-Emitter Saturation Voltage vs Ambient Temperature

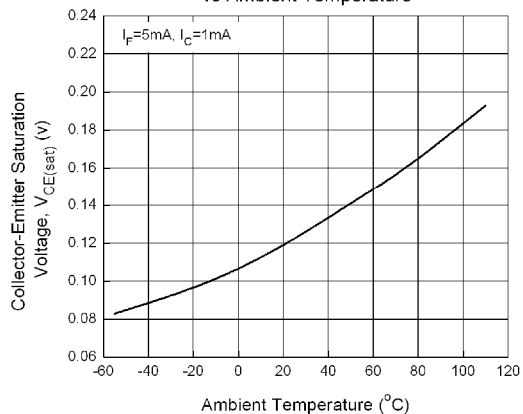


Figure 10. Switching Time vs Load Resistance

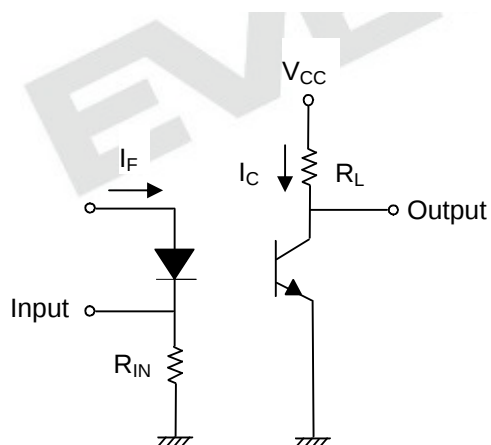
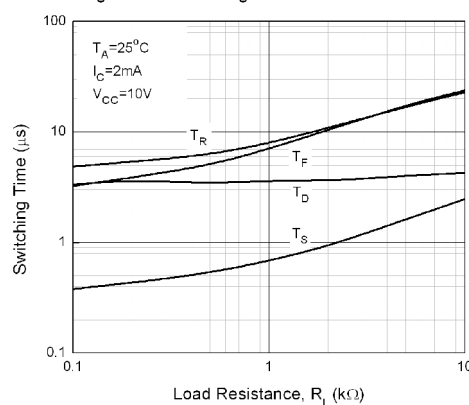


Figure 11. Switching Time Test Circuit & Waveforms

Order Information**Part Number****EL3H7(X)(Y)-VG****Note**

3H7 = Part No.

X = CTR Rank (A, B, C, D, E, F, H, I, J, K or none)

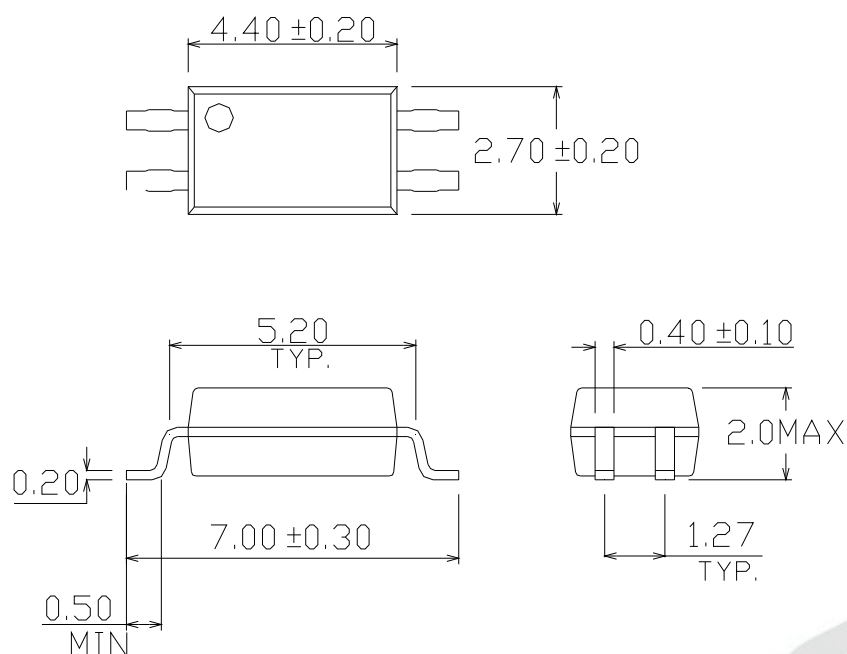
Y = Tape and reel option (TA, TB, EA, EB or none).

V = VDE (optional)

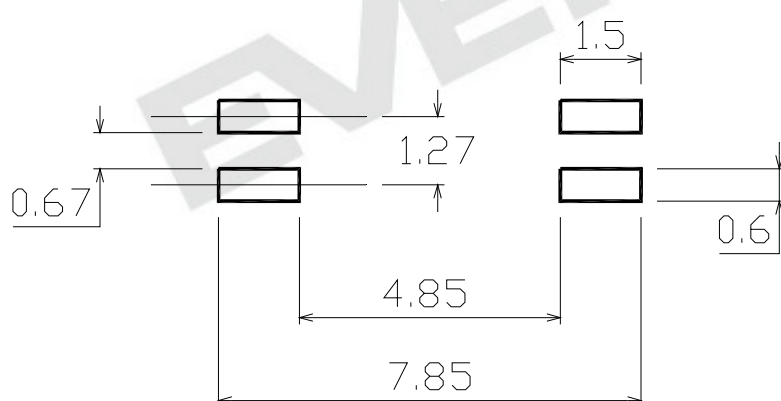
G = Halogens free

Option	Description	Packing quantity
None	Standard SMD option	100 units per tube
-V	Standard SMD option + VDE	100 units per tube
(TA)	TA Tape & reel option	5000 units per reel
(TB)	TB Tape & reel option	5000 units per reel
(TA)-V	TA Tape & reel option + VDE	5000 units per reel
(TB)-V	TB Tape & reel option + VDE	5000 units per reel
(EA)	TA Tape & reel option	1000 units per reel
(EB)	TB Tape & reel option	1000 units per reel
(EA)-V	TA Tape & reel option + VDE	1000 units per reel
(EB)-V	TB Tape & reel option + VDE	1000 units per reel

Package Drawing
(Dimensions in mm)



Recommended pad layout for surface mount leadform



Device Marking



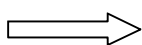
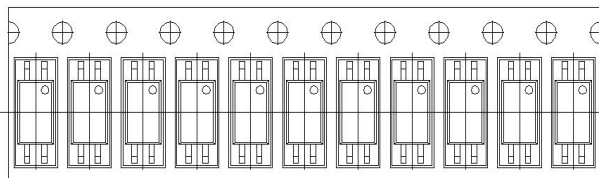
Notes

EL	denotes Everlight
3H7	denotes Device Number
R	denotes CTR Rank (A, B, C, D, E, F, H, I, J, K or none)
Y	denotes 1 digit Year code
WW	denotes 2 digit Week code
V	denotes VDE (optional)

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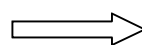
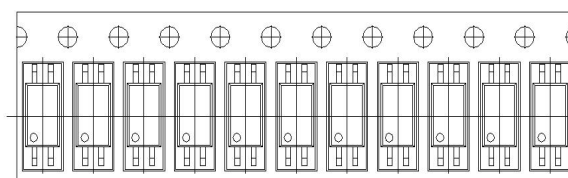
Tape & Reel Packing Specifications

Option TA



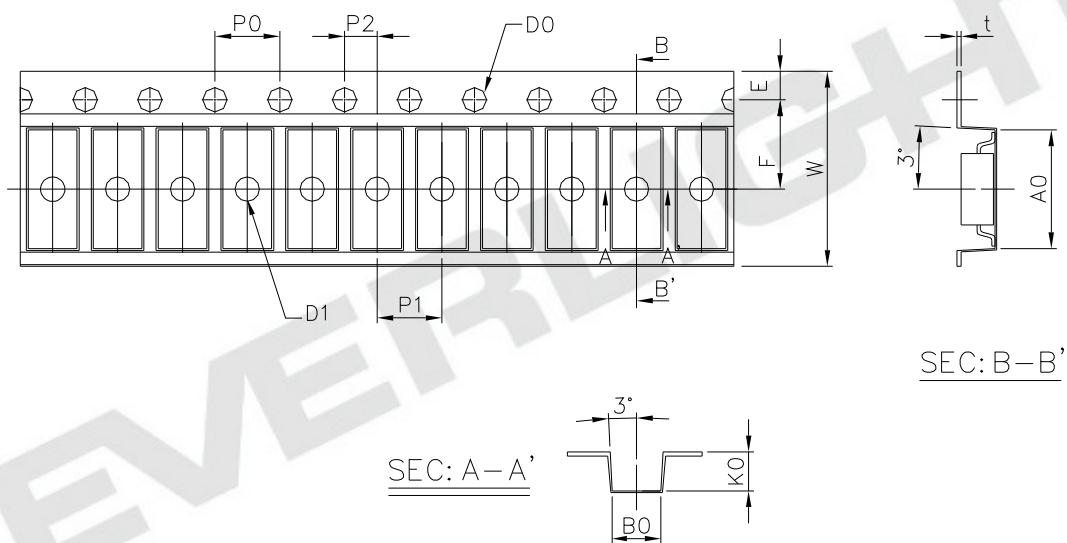
Direction of feed from reel

Option TB



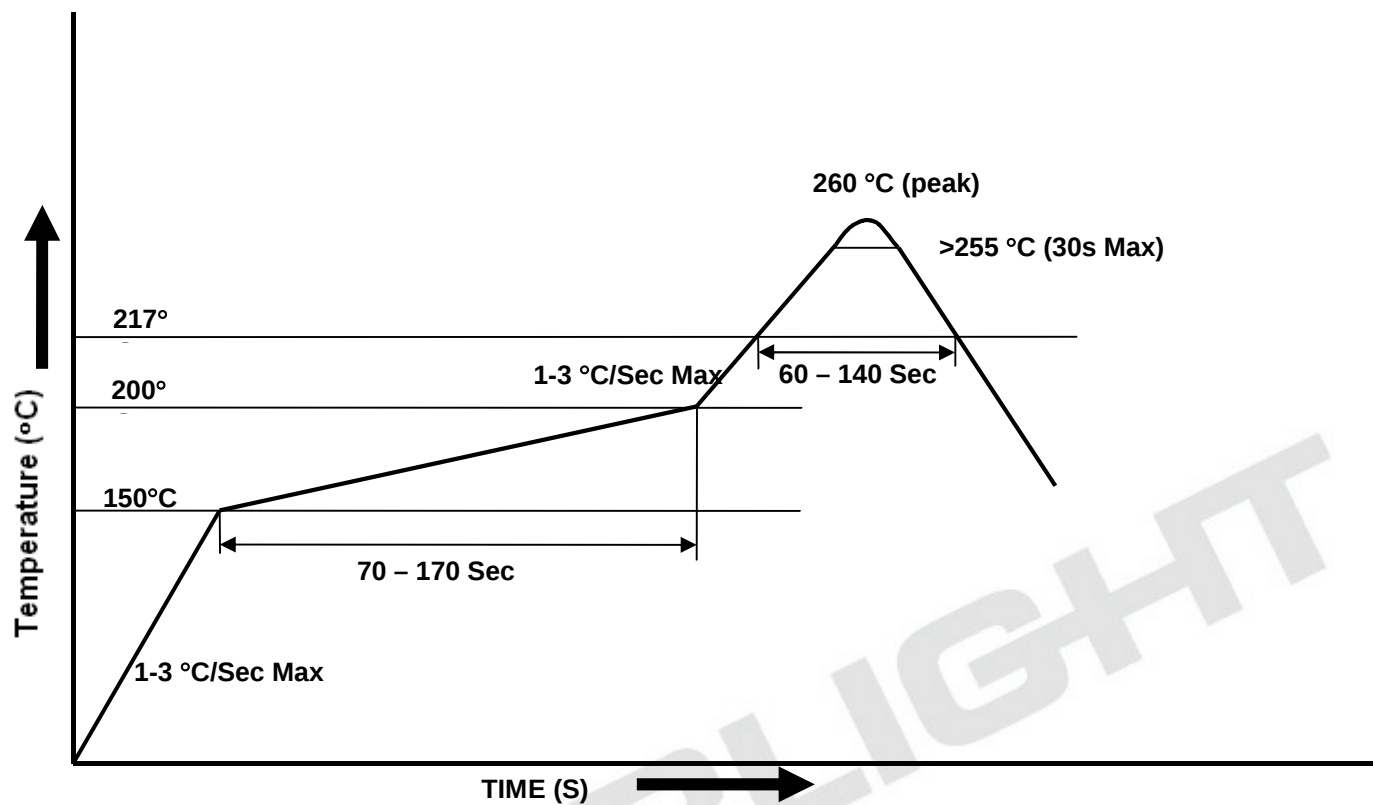
Direction of feed from reel

Tape dimensions



Dimension No.	A	B	Do	D1	E	F
Dimension (mm)	3.0 ± 0.1	7.3 ± 0.1	$1.5 + 0.1/-0$	1.5 ± 0.1	1.75 ± 0.1	5.5 ± 0.1

Dimension No.	Po	P1	P2	t	W	K
Dimension (mm)	4.0 ± 0.15	4.0 ± 0.1	2.0 ± 0.1	0.25 ± 0.03	12.0 ± 0.2	2.4 ± 0.1

Solder Reflow Temperature Profile

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